

PBSS3515E

15 V, 0.5 A PNP low V_{CEsat} (BISS) transistor

Rev. 01 — 18 April 2005

Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough in Small Signal (BISS) transistor in a SOT416 (SC-75) SMD plastic package.

NPN complement: PBSS2515E.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- Low power switches (e.g. motors, fans)
- Portable applications

1.4 Quick reference data

Table 1: Quick reference data

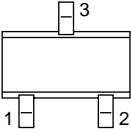
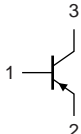
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-15	V
I_C	collector current (DC)		-	-	-0.5	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-1	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500$ mA; $I_B = -50$ mA	[1] -	300	500	m Ω

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

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2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter		
3	collector		

sym013

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PBSS3515E	SC-75	plastic surface mounted package; 3 leads	SOT416

4. Marking

Table 4: Marking codes

Type number	Marking code
PBSS3515E	1R

5. Limiting values

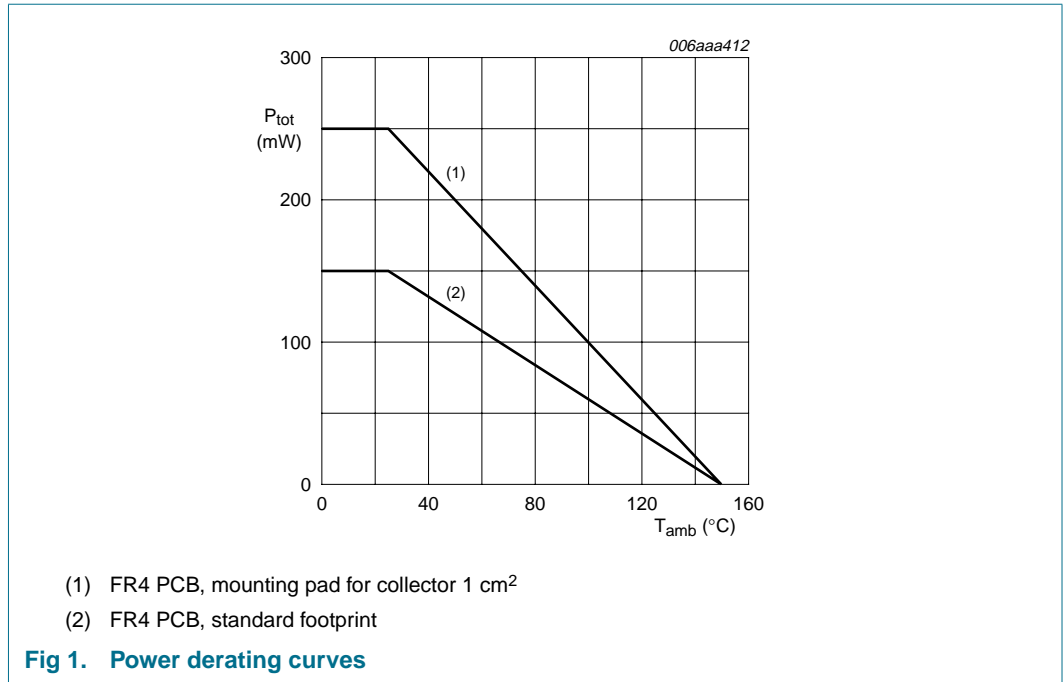
Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-15	V
V_{CEO}	collector-emitter voltage	open base	-	-15	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I_C	collector current (DC)		-	-0.5	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-1	A
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	-100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	150	mW
			[2]	250	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	833	K/W
			[2]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

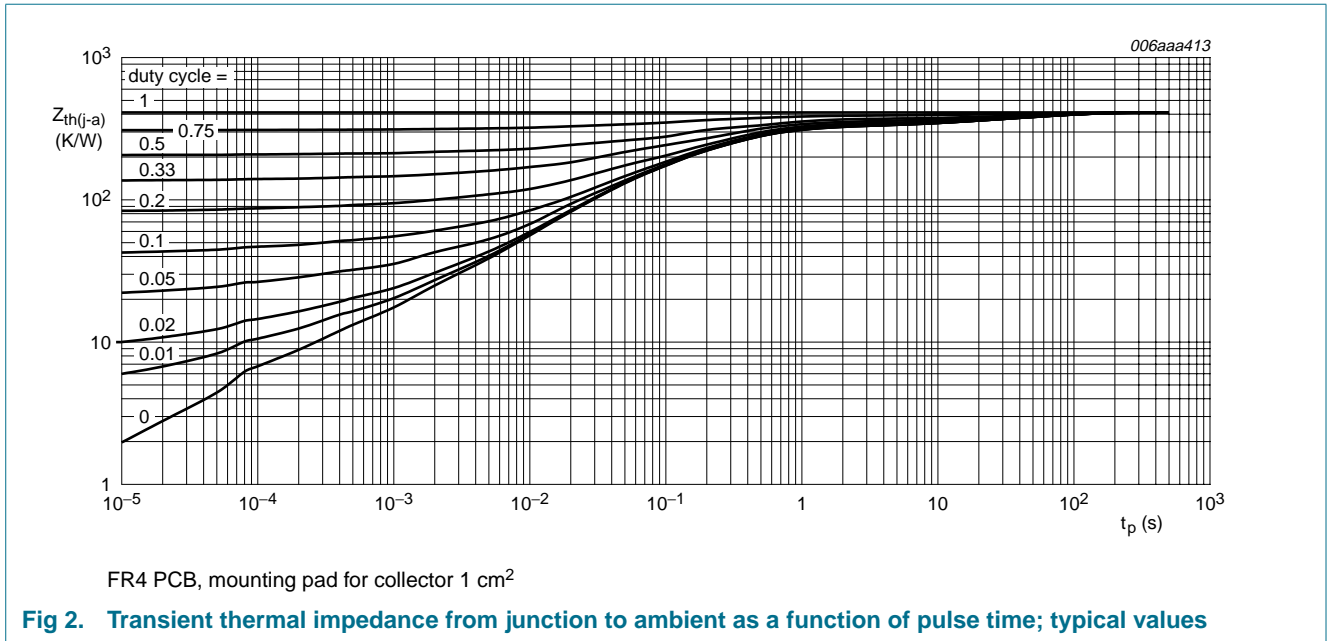


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

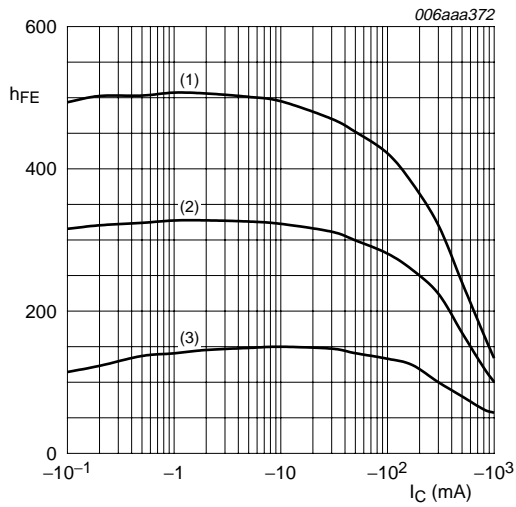
7. Characteristics

Table 7: Characteristics

$T_{amb} = 25\text{ }^\circ\text{C}$ unless otherwise specified.

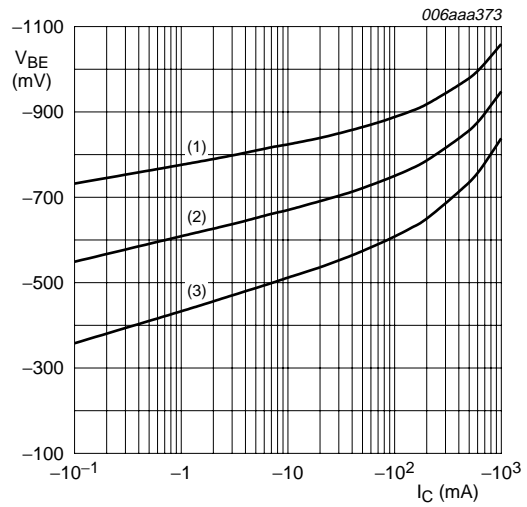
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -15\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
		$V_{CB} = -15\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^\circ\text{C}$	-	-	-50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}; I_C = -10\text{ mA}$	200	-	-	
		$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	[1] 150	-	-	
		$V_{CE} = -2\text{ V}; I_C = -500\text{ mA}$	[1] 90	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	-	-	-25	mV
		$I_C = -200\text{ mA}; I_B = -10\text{ mA}$	-	-	-150	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1] -	-	-250	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1] -	300	500	m Ω
V_{BEsat}	base-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1] -	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	[1] -	-	-0.9	V
f_T	transition frequency	$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}; f = 100\text{ MHz}$	100	280	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	10	pF

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



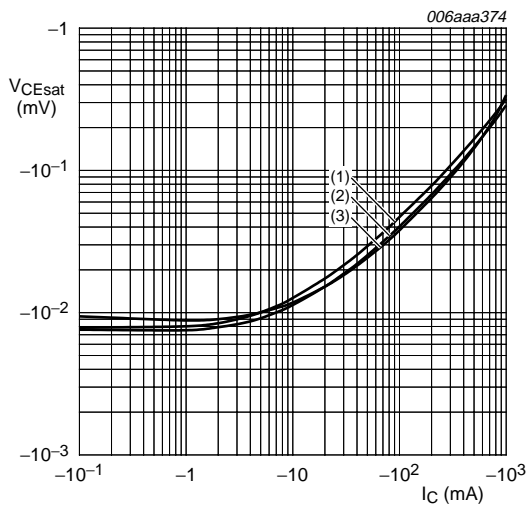
$V_{CE} = -2\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig 3. DC current gain as a function of collector current; typical values



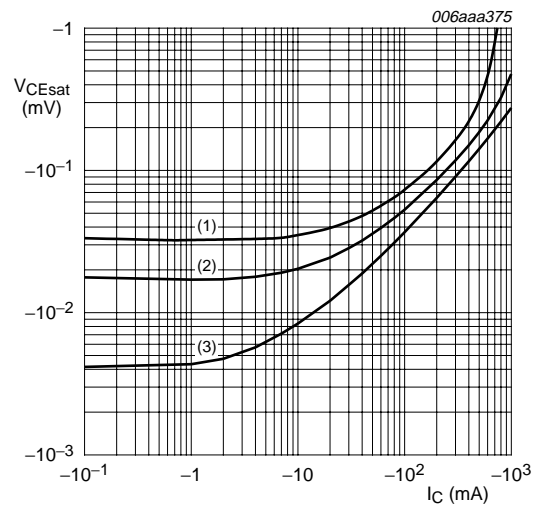
$V_{CE} = -2\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig 4. Base-emitter voltage as a function of collector current; typical values



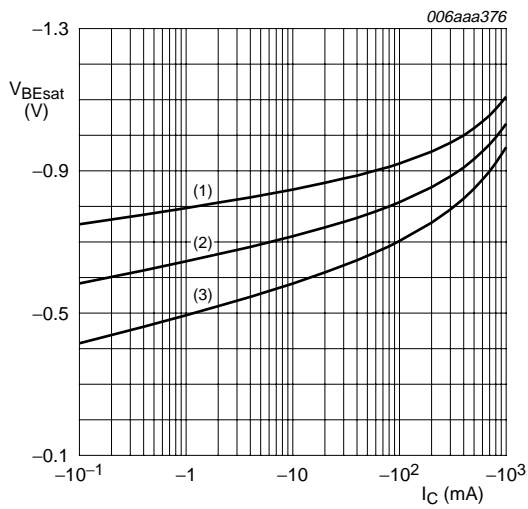
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



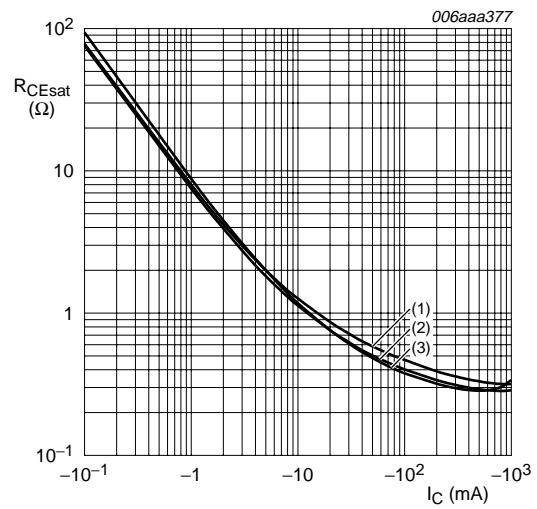
$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values



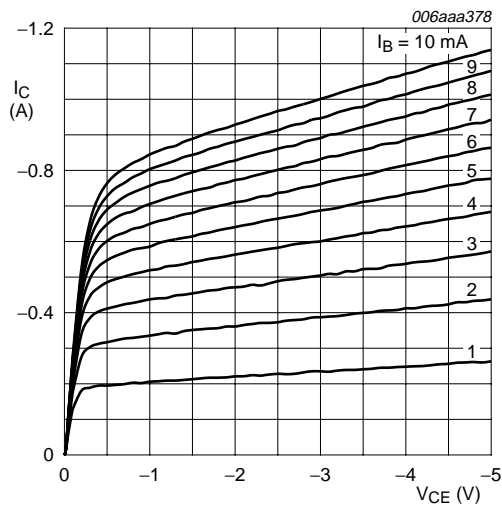
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values



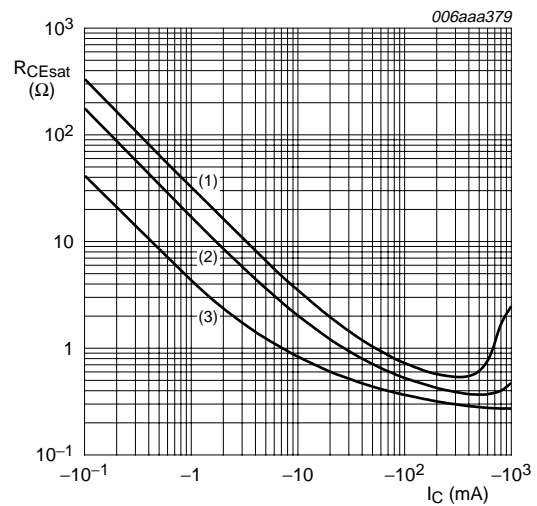
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 8. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$

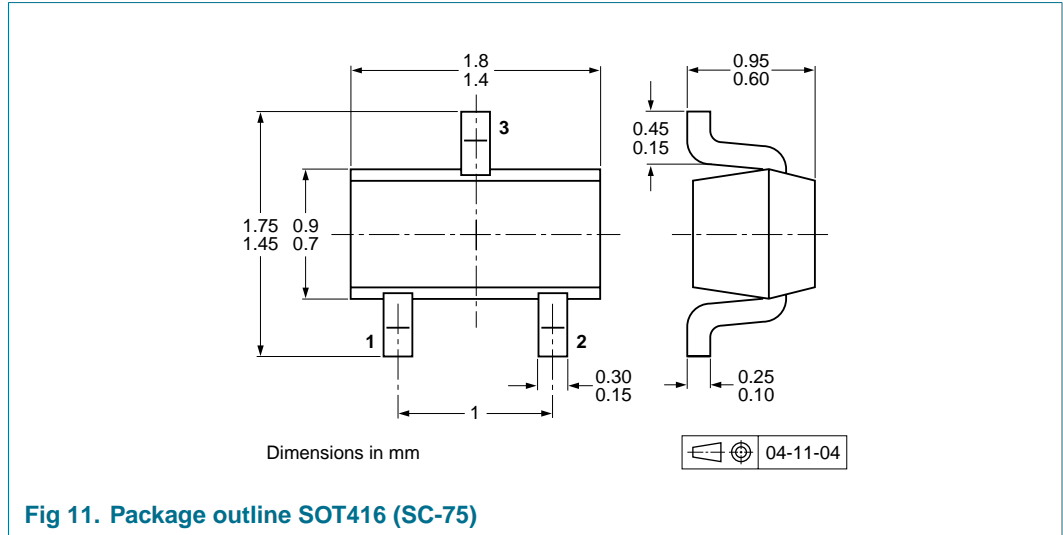
Fig 9. Collector current as a function of collector-emitter voltage; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

8. Package outline



9. Packing information

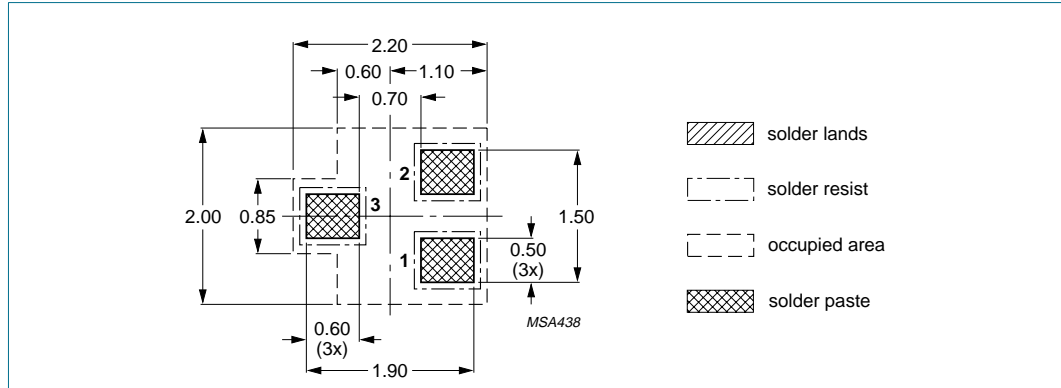
Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBSS3515E	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135

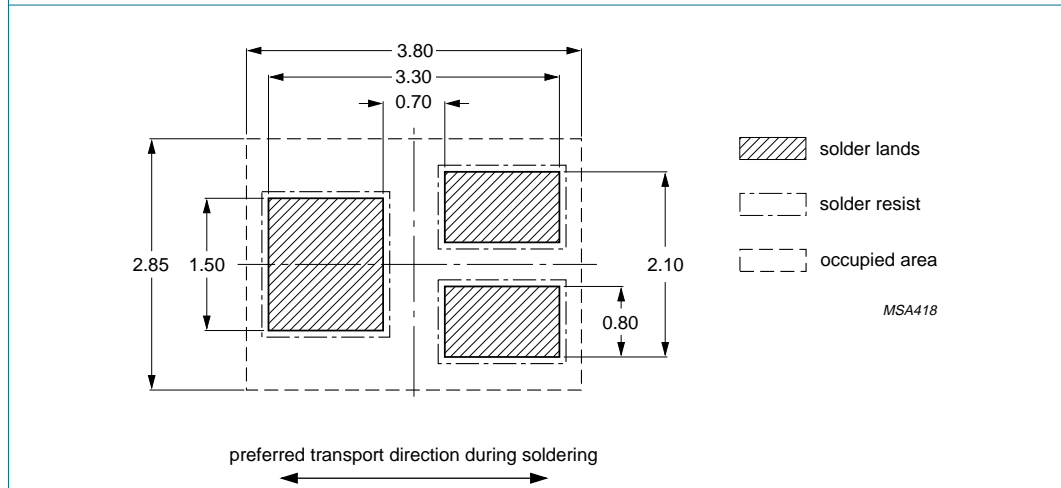
[1] For further information and the availability of packing methods, see [Section 15](#).

10. Soldering



Dimensions in mm

Fig 12. Reflow soldering footprint



Dimensions in mm

Fig 13. Wave soldering footprint

11. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PBSS3515E_1	20050418	Product data sheet	-	9397 750 14878	-

12. Data sheet status

Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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